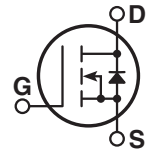
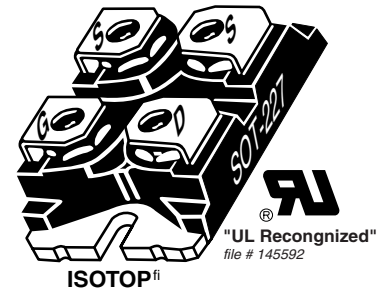


## Super Junction MOSFET



- Ultra low  $R_{DS(ON)}$
- Ultra Low Gate Charge,  $Q_g$
- Popular SOT-227 Package
- Low Miller Capacitance
- Avalanche Energy Rated
- N-Channel Enhancement Mode



Unless stated otherwise, Microsemi discrete MOSFETs contain a single MOSFET die. This device is made with two parallel MOSFET die. It is intended for switch-mode operation. It is not suitable for linear mode operation.

### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

| Symbol         | Parameter  | APT77N60JC3 | UNIT                |
|----------------|--|-------------|---------------------|
| $V_{DSS}$      | Drain-Source Voltage   | 600         | Volts               |
| $I_D$          | Continuous Drain Current @ $T_C = 25^\circ\text{C}$  | 77          | Amps                |
| $I_{DM}$       | Pulsed Drain Current <sup>①</sup>  | 231         |                     |
| $V_{GS}$       | Gate-Source Voltage Continuous   | $\pm 20$    | Volts               |
| $V_{GSM}$      | Gate-Source Voltage Transient  | $\pm 30$    |                     |
| $P_D$          | Total Power Dissipation @ $T_C = 25^\circ\text{C}$   | 568         | Watts               |
|                | Linear Derating Factor   | 4.55        | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Junction Temperature Range   | -55 to 150  | $^\circ\text{C}$    |
| $T_L$          | Lead Temperature: 0.063" from Case for 10 Sec.   | 300         |                     |
| $dv/dt$        | Drain-Source Voltage slope ( $V_{DS} = 480\text{V}$ , $I_D = 77\text{A}$ , $T_J = 125^\circ\text{C}$ ) | 50          | V/ns                |
| $I_{AR}$       | Repetitive Avalanche Current <sup>⑦</sup>  | 20          | Amps                |
| $E_{AR}$       | Repetitive Avalanche Energy <sup>⑦</sup>   | 1           | mJ                  |
| $E_{AS}$       | Single Pulse Avalanche Energy <sup>④</sup>   | 1800        |                     |

### STATIC ELECTRICAL CHARACTERISTICS

| Symbol       | Characteristic / Test Conditions  | MIN | TYP  | MAX       | UNIT          |
|--------------|---|-----|------|-----------|---------------|
| $BV_{DSS}$   | Drain-Source Breakdown Voltage ( $V_{GS} = 0\text{V}$ , $I_D = 500\mu\text{A}$ )                          | 600 |      |           | Volts         |
| $R_{DS(on)}$ | Drain-Source On-State Resistance <sup>②</sup> ( $V_{GS} = 10\text{V}$ , $I_D = 60\text{A}$ )              |     | .030 | 0.035     | Ohms          |
| $I_{DSS}$    | Zero Gate Voltage Drain Current ( $V_{DS} = V_{DSS}$ , $V_{GS} = 0\text{V}$ )                             |     | 1.0  | 50        | $\mu\text{A}$ |
|              | Zero Gate Voltage Drain Current ( $V_{DS} = V_{DSS}$ , $V_{GS} = 0\text{V}$ , $T_J = 150^\circ\text{C}$ ) |     |      | 500       |               |
| $I_{GSS}$    | Gate-Source Leakage Current ( $V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$ )                          |     |      | $\pm 200$ | nA            |
| $V_{GS(th)}$ | Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 5.4\text{mA}$ )                                       | 2.1 | 3    | 3.9       | Volts         |

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Microsemi Website - <http://www.microsemi.com>

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# DYNAMIC CHARACTERISTICS

APT77N60JC3

| Symbol       | Characteristic                        | Test Conditions   | MIN | TYP   | MAX | UNIT    |
|--------------|---------------------------------------|---|-----|-------|-----|---------|
| $C_{iss}$    | Input Capacitance                     | $V_{GS} = 0V$<br>$V_{DS} = 25V$<br>$f = 1\text{ MHz}$   |     | 13600 |     | pF      |
| $C_{oss}$    | Output Capacitance                    |   |     | 4400  |     |         |
| $C_{rss}$    | Reverse Transfer Capacitance          |   |     | 290   |     |         |
| $Q_g$        | Total Gate Charge <sup>③</sup>        | $V_{GS} = 10V$<br>$V_{DD} = 300V$<br>$I_D = 77A @ 25^\circ C$   |     | 505   | 640 | nC      |
| $Q_{gs}$     | Gate-Source Charge                    |   |     | 48    |     |         |
| $Q_{gd}$     | Gate-Drain ("Miller") Charge          |   |     | 240   |     |         |
| $t_{d(on)}$  | Turn-on Delay Time                    | <b>RESISTIVE SWITCHING</b><br>$V_{GS} = 10V$<br>$V_{DD} = 380V$<br>$I_D = 77A @ 125^\circ C$<br>$R_G = 0.9\Omega$ |     | 18    |     | ns      |
| $t_r$        | Rise Time                             |   |     | 27    |     |         |
| $t_{d(off)}$ | Turn-off Delay Time                   |   |     | 110   | 165 |         |
| $t_f$        | Fall Time                             |   |     | 8     | 12  |         |
| $E_{on}$     | Turn-on Switching Energy <sup>⑥</sup> | <b>INDUCTIVE SWITCHING @ 25°C</b><br>$V_{DD} = 400V, V_{GS} = 15V$<br>$I_D = 77A, R_G = 5\Omega$                  |     | 1670  |     | $\mu J$ |
| $E_{off}$    | Turn-off Switching Energy             |   |     | 2880  |     |         |
| $E_{on}$     | Turn-on Switching Energy <sup>⑥</sup> | <b>INDUCTIVE SWITCHING @ 125°C</b><br>$V_{DD} = 400V, V_{GS} = 15V$<br>$I_D = 77A, R_G = 5\Omega$                 |     | 2300  |     |         |
| $E_{off}$    | Turn-off Switching Energy             |   |     | 3100  |     |         |

# SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

| Symbol   | Characteristic / Test Conditions   | MIN | TYP | MAX | UNIT    |
|----------|--|-----|-----|-----|---------|
| $I_S$    | Continuous Source Current (Body Diode)                                     |     |     | 77  | Amps    |
| $I_{SM}$ | Pulsed Source Current <sup>①</sup> (Body Diode)                            |     |     | 231 | Amps    |
| $V_{SD}$ | Diode Forward Voltage <sup>②</sup> ( $V_{GS} = 0V, I_S = -77A$ )           |     | 1   | 1.2 | Volts   |
| $t_{rr}$ | Reverse Recovery Time ( $I_S = -77A, di_S/dt = 100A/\mu s, V_R = 350V$ )   |     | 861 |     | ns      |
| $Q_{rr}$ | Reverse Recovery Charge ( $I_S = -77A, di_S/dt = 100A/\mu s, V_R = 350V$ ) |     | 46  |     | $\mu C$ |
| $dv/dt$  | Peak Diode Recovery $dv/dt$ <sup>⑤</sup>                                   |     |     | 6   | V/ns    |

# THERMAL CHARACTERISTICS

| Symbol          | Characteristic      | MIN | TYP | MAX  | UNIT         |
|-----------------|---------------------|-----|-----|------|--------------|
| $R_{\theta JC}$ | Junction to Case    |     |     | 0.22 | $^\circ C/W$ |
| $R_{\theta JA}$ | Junction to Ambient |     |     | 40   | $^\circ C/W$ |

① Repetitive Rating: Pulse width limited by maximum junction temperature

② Pulse Test: Pulse width < 380  $\mu s$ , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting  $T_J = +25^\circ C, L = 36.0mH, R_G = 25\Omega, \text{Peak } I_L = 10A$

⑤  $dv/dt$  numbers reflect the limitations of the test circuit rather than the device itself.  $I_S \leq -I_D 77A, di/dt \leq 700A/\mu s, V_R \leq V_{DSS}, T_J \leq 150^\circ C$

⑥  $E_{on}$  includes diode reverse recovery. See figures 18, 20.

⑦ Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV} = E_{AR} \cdot f$

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

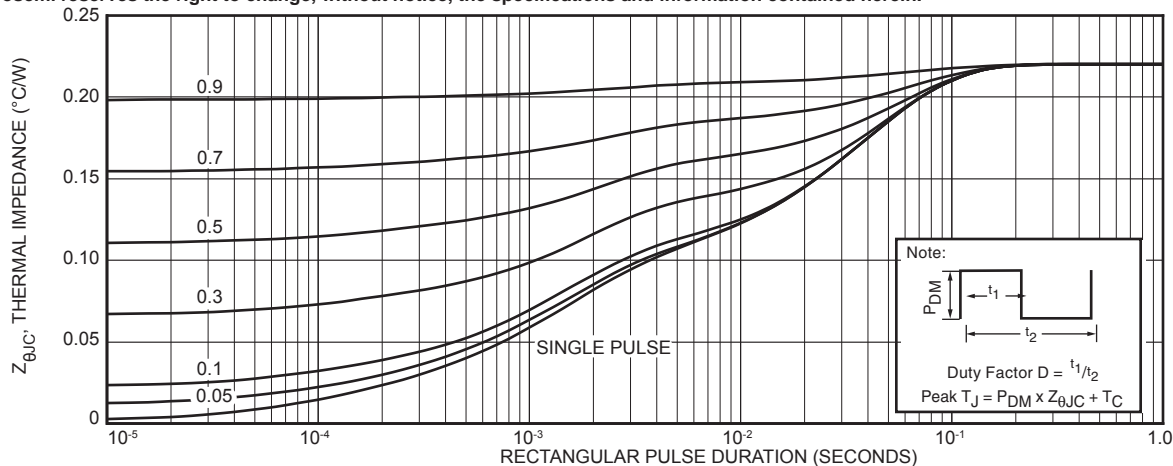


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

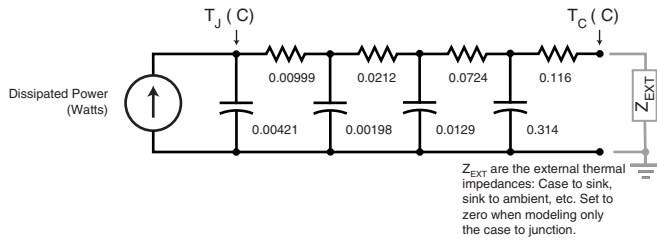


FIGURE 2, TRANSIENT THERMAL IMPEDANCE MODEL

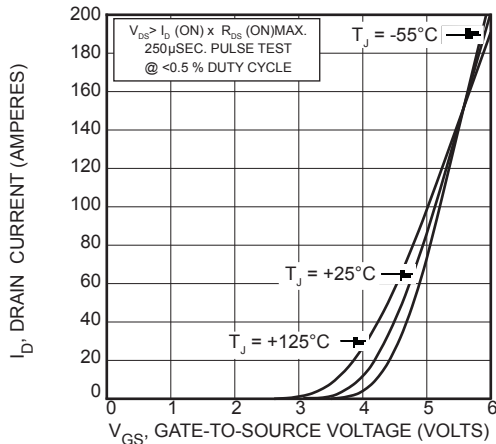


FIGURE 4, TRANSFER CHARACTERISTICS

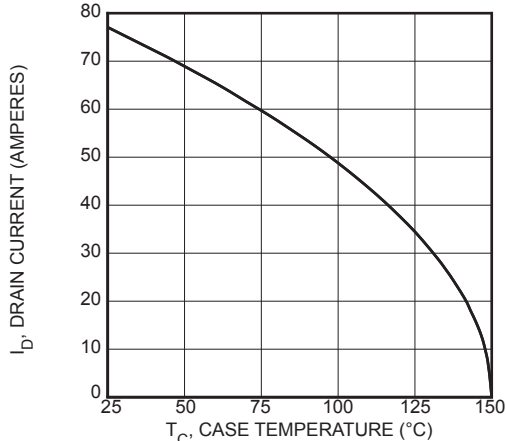


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

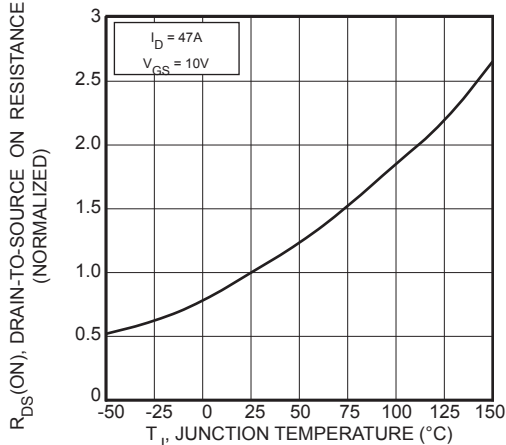


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

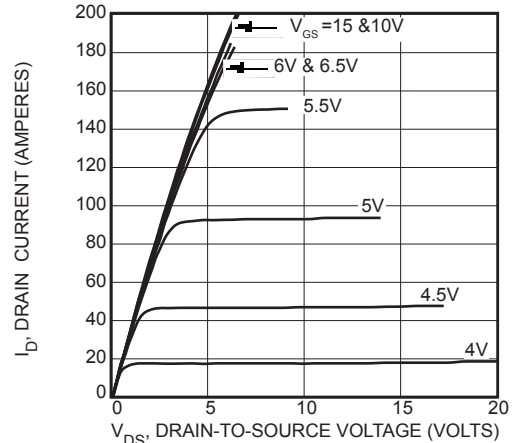


FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS

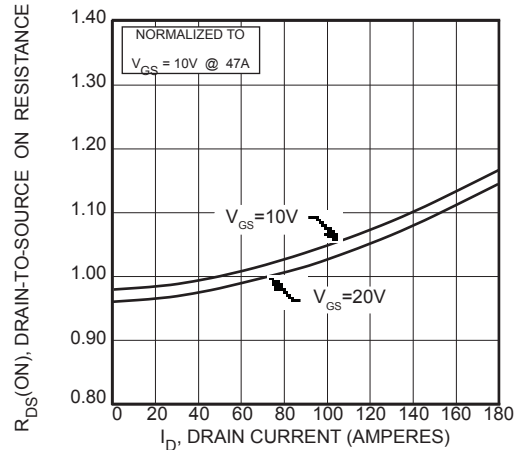


FIGURE 5,  $R_{DS(ON)}$  vs DRAIN CURRENT

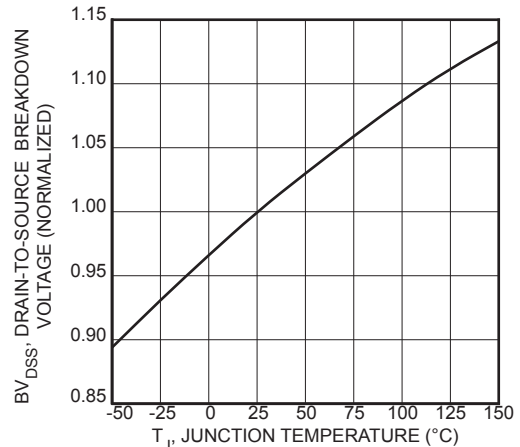


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

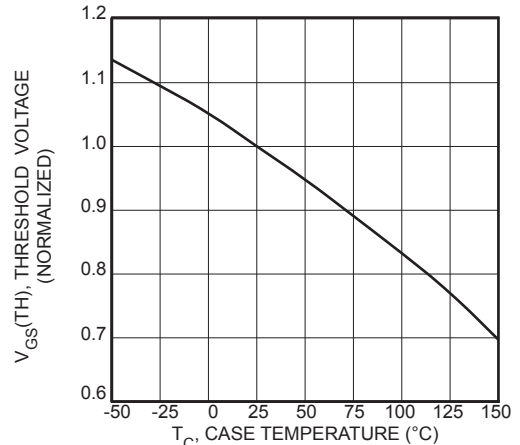


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

Typical Performance

APT77N60JC3

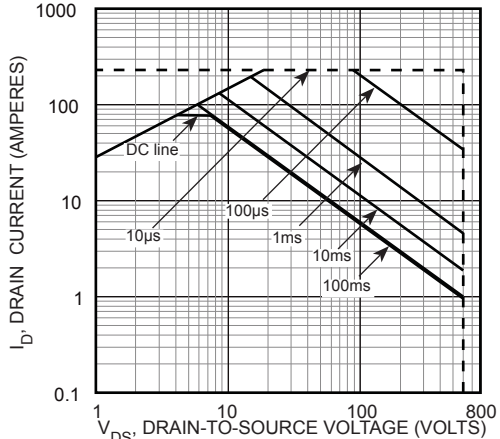


FIGURE 10, MAXIMUM SAFE OPERATING AREA

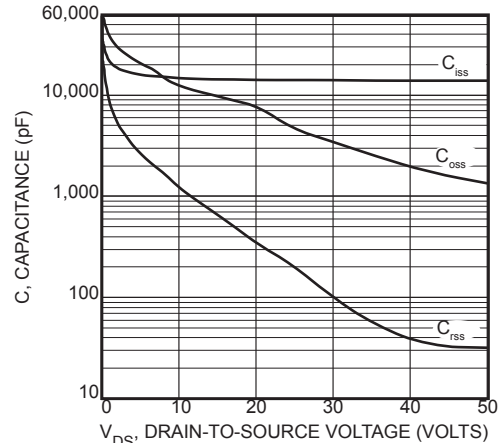


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

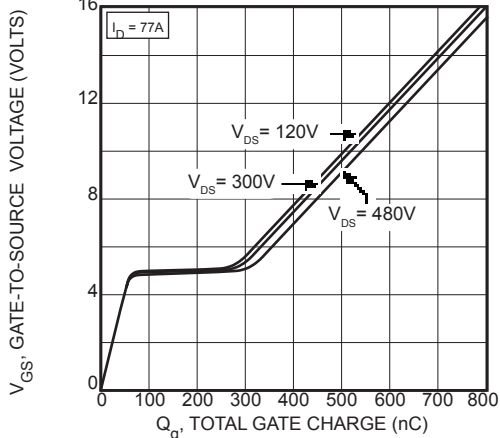


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

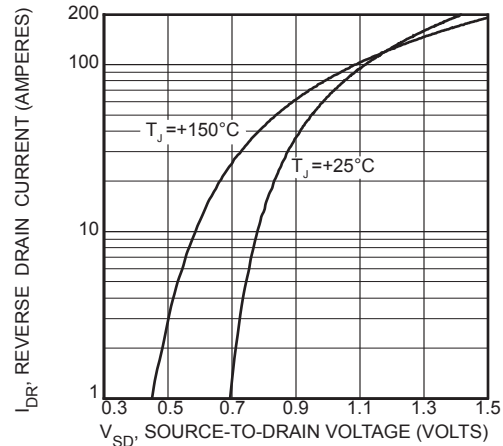


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

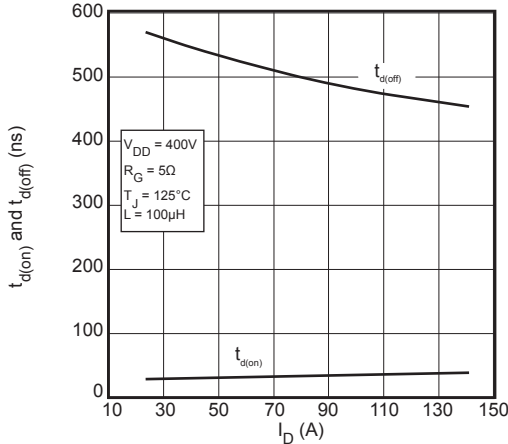


FIGURE 14, DELAY TIMES vs CURRENT

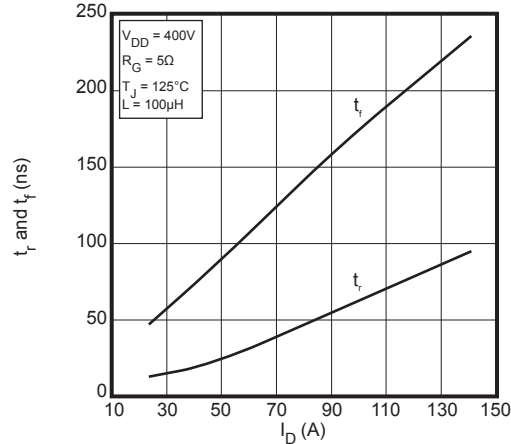


FIGURE 15, RISE AND FALL TIMES vs CURRENT

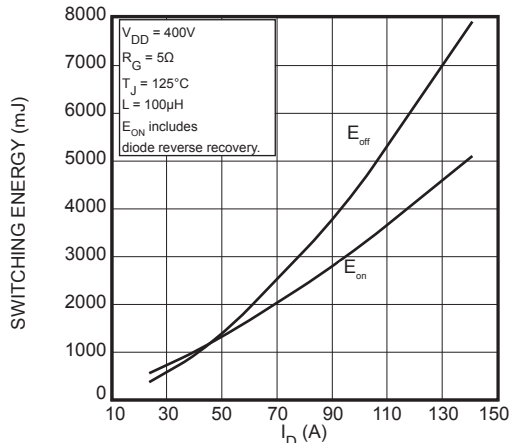


FIGURE 16, SWITCHING ENERGY vs CURRENT

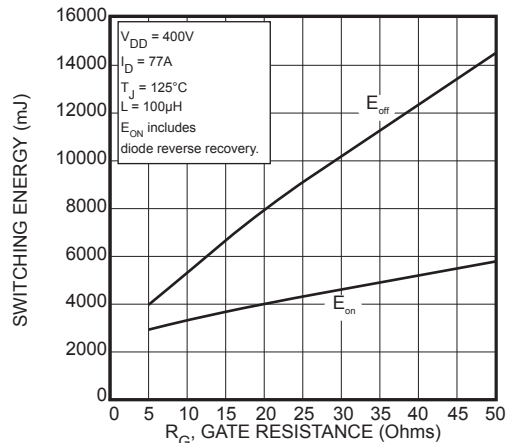


FIGURE 17, SWITCHING ENERGY vs. GATE RESISTANCE

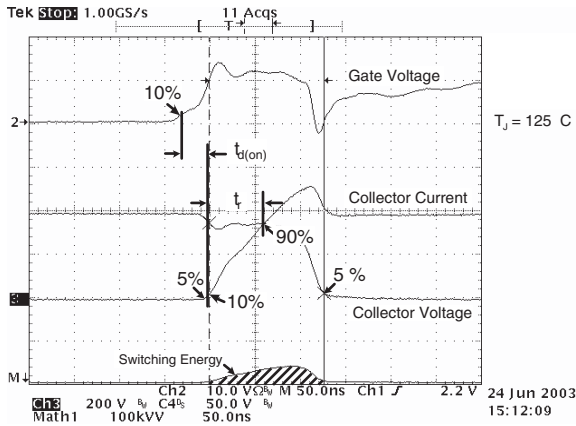


Figure 18, Turn-on Switching Waveforms and Definitions

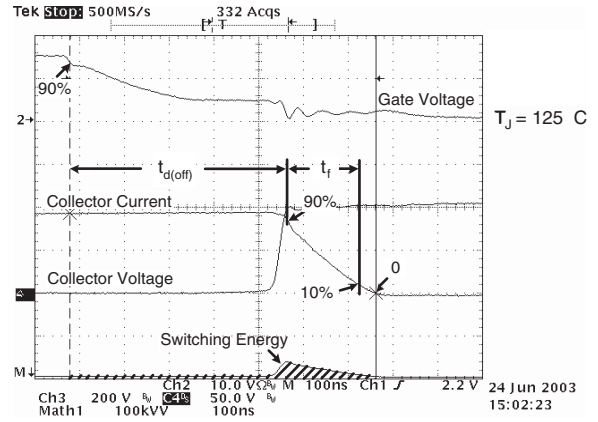


Figure 19, Turn-off Switching Waveforms and Definitions

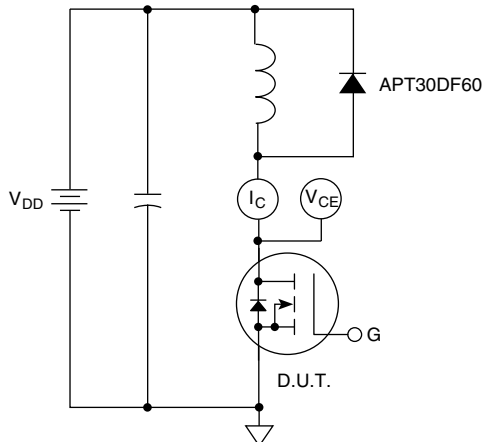
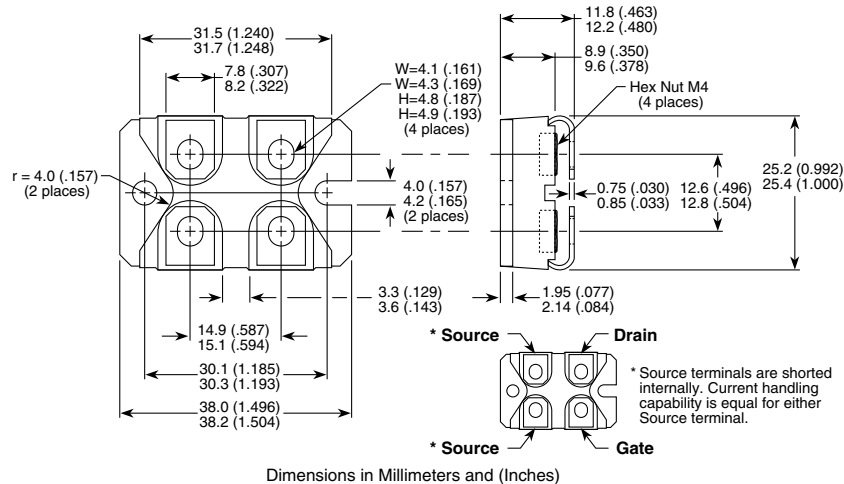


Figure 20, Inductive Switching Test Circuit

SOT-227 (ISOTOP®) Package Outline



Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743, 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. US and Foreign patents pending. All Rights Reserved.

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